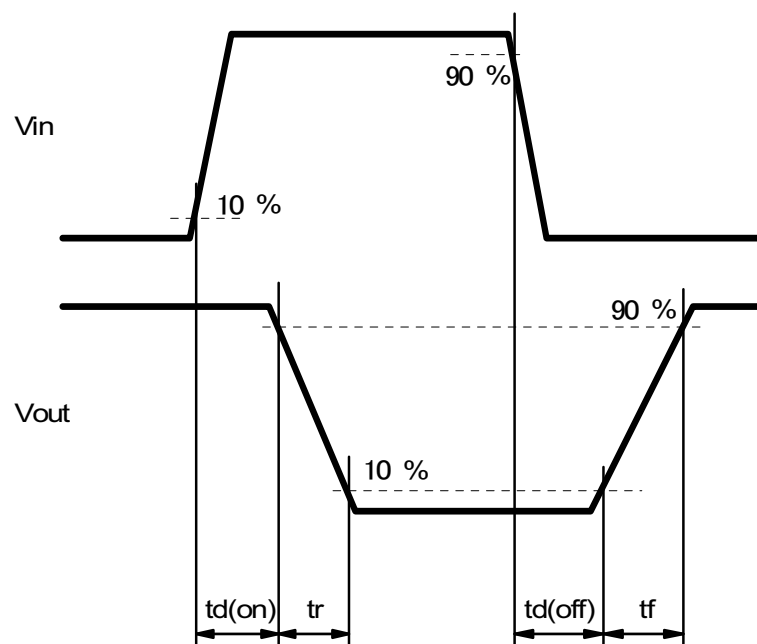
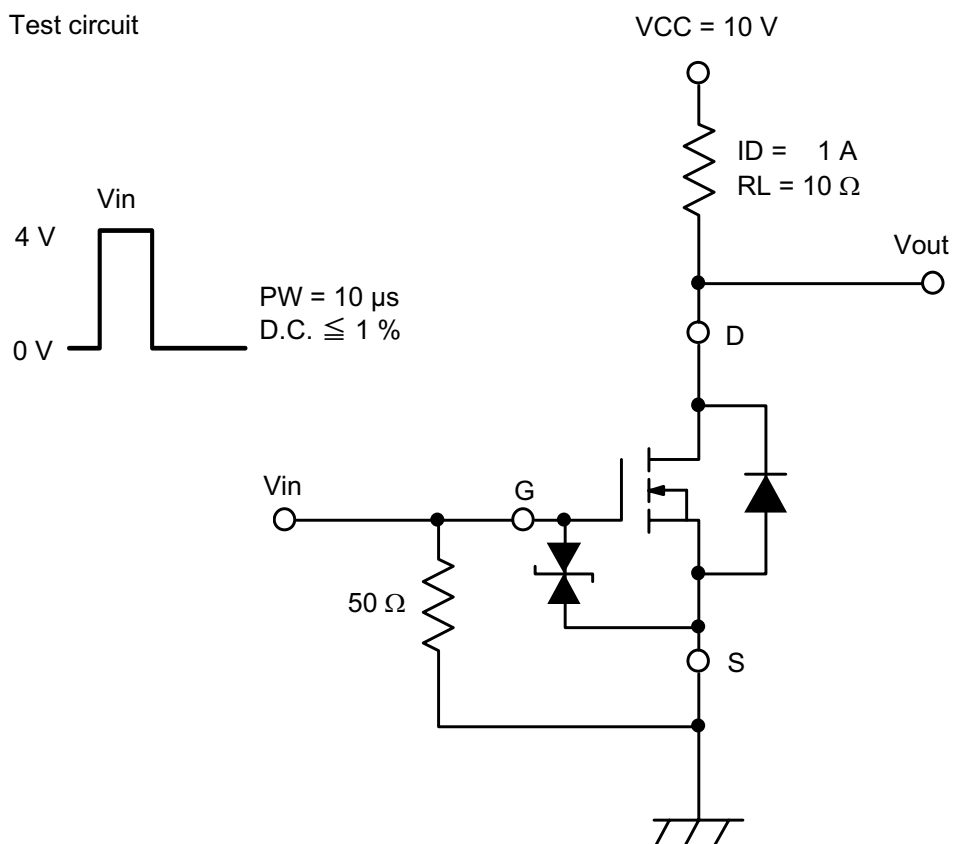


Product Specification TYPE NUMBER : M T M 8 6 7 2 7 0 L B F *1					Prepared by S.Miyata	Checked by M.Fujisawa	Applied by H.Shidooka	Established by K.Kemichi	
Type	Silicon Field Effect Transistors								
Application	Switching								
Structure	N-Channel MOS Type								
Outline	WSSMini6 - F1					Marking		JE	
Absolute Maximum Ratings	VDSS 20 (V)	VGSS ±10 (V)	ID 2.2 (A)	IDp 8.0 (A)	*2 PD 540 (mW)	Tch 150 (°C)	Tstg -55 to +150 (°C)		
Electrical characteristics (Ta=25 °C ±3 °C)									
Item	Symbol	Measuring condition	Limit			Unit			
			min.	typ.	max.				
Drain-Source Voltage	VDSS	ID = 1 mA, VGS = 0 V	20			V			
Drain-Source Cutoff Current	IDSS	VDS = 20 V, VGS = 0 V			1.0	μA			
Gate-Source Cutoff Current	IGSS	VGS = ±8 V, VDS = 0 V			±10	μA			
Gate Threshold Voltage	Vth	ID = 1.0 mA, VDS = 10 V	0.4	0.85	1.3	V			
Drain Resistance (ON) 1	RDS(ON) 1	ID = 1 A, VGS = 4.0 V		80	105	mΩ			
Drain Resistance (ON) 2	RDS(ON) 2	ID = 0.5 A, VGS = 2.5 V		100	150	mΩ			
Forward Transfer Admittance	Yfs	ID = 1.0 A, VDS = 10 V	3.0			S			
Small-Signal Short-Circuit Input Capacitance	Ciss	VDS = 10 V, VGS = 0, f = 1 MHz		280		pF			
Small-Signal Short-Circuit Output Capacitance	Coss	VDS = 10 V, VGS = 0, f = 1 MHz		18		pF			
Small-Signal Reverse Transfer Capacitance	Crss	VDS = 10 V, VGS = 0, f = 1 MHz		17		pF			
Turn-on Delay Time	td(on) *3	VDD = 10 V, VGS = 0 to 4 V, ID = 1 A		5		ns			
Rise Time	tr *3	VDD = 10 V, VGS = 0 to 4 V, ID = 1 A		8		ns			
Turn-off Delay Time	td(off) *3	VDD = 6 V, VGS = 4 to 0 V, ID = 1 A		20		ns			
Fall Time	tf *3	VDD = 6 V, VGS = 4 to 0 V, ID = 1 A		18		ns			
Note: Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors. *1 Packing Embossed TX Type (Thermo-compression sealing) *2 Measuring on Ceramic substrate at 40×38×0.2mm. Absolute maximum rating PD without heat sink shall be made 150mW. *3 See test circuit							Internally connected circuit 1 (G) 2 (S) 3 (A) (D) 6 (D) 5 (K) 4		
2008.01.31									
Established		Revised							

Product Specification

TYPE NUMBER : M T M 8 6 7 2 7 0 L B F
*1

Test circuit



2008.01.31

Established

Revised

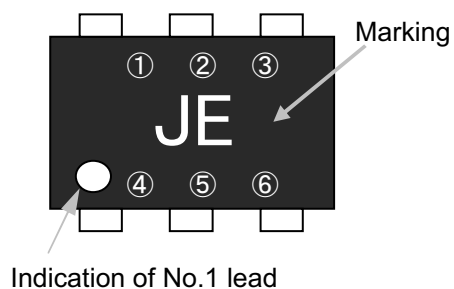
Product Specification						
TYPE NUMBER : M T M 8 6 7 2 7 0 L B F						
*1						
Type	Schottky Barrier Diode					
Application	High Speed Switching					
Structure	Si Epitaxial Planar Type					
Outline	WSSMini6 - F1					
Absolute Maximum Ratings	IF(AV)	*3 IFSM	VR	Tj	Tstg	
	800	3	20	125	-55 to +125	
	(mA)	(A)	(V)	(°C)	(°C)	
Electrical characteristics (Ta=25 °C ±3 °C)						
Item	Symbol	Measuring condition	Limit			Unit
			min.	typ.	max.	
Forward Voltage	VF	IF = 800 mA			0.47	V
Reverse Current	IR	VR = 20 V			80	μA
Note:						
Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for diodes.						
*3 50 Hz Sine Wave 1 Cycle (Non-Repetitive Peak Current)						

Product Specification

Mark Indication

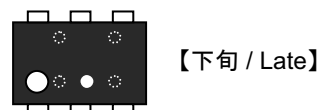
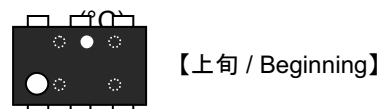
TYPE NUMBER : M T M 8 6 7 2 7 0 L B F

*1

Mark layout

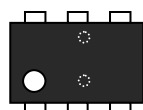
①③④⑥ : Indication of produced month
 ②⑤ : Display position of beginning/middle
 /late month indication

《②⑤ : Example of indication of
 beginning/middle/late month indication 》

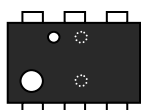


The actual font of product symbol may differ slightly
 from the font shown in this specification.

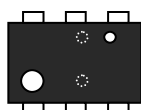
《Example of indication of produced month 》



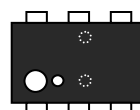
【Jan.】



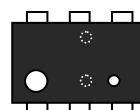
【Feb.】



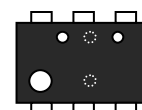
【Mar.】



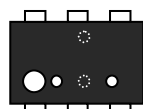
【Apr.】



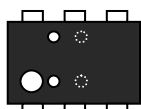
【May】



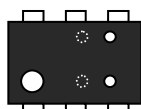
【Jun.】



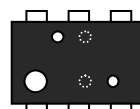
【Jul.】



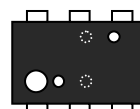
【Aug.】



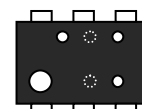
【Sep.】



【Oct.】



【Nov.】



【Dec.】

・ Factory distinction mark

Factory	JAPAN
Package code	WSSMini6 - F1
Marking	No indication 

※ White parts are treated by laser mark.

2008.01.31

Established

Revised